

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Lead Free By Design/RoHS Compliant (Note 2)**
- **ESD Protected Gate**
- **"Green" Device (Note 4)**
- **Qualified to AEC-Q101 standards for High Reliability**

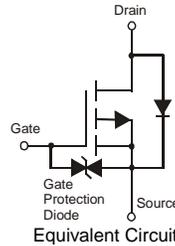


ESD PROTECTED

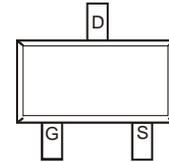


TOP VIEW

SOT-523



Equivalent Circuit



TOP VIEW

Mechanical Data

- Case: SOT-523
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish - Matte Tin annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.002 grams (approximate)

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

| Characteristic | | | Symbol | Value | Units |
|-------------------------------|--------------|--------------------------|-----------|---------|-------|
| Drain-Source Voltage | | | V_{DSS} | -20 | V |
| Gate-Source Voltage | | | V_{GSS} | ± 8 | V |
| Drain Current (Note 1) | Steady State | $T_A = 25^\circ\text{C}$ | I_D | -430 | mA |
| | | $T_A = 85^\circ\text{C}$ | | -310 | |
| Pulsed Drain Current (Note 3) | | | I_{DM} | -750 | mA |

Thermal Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

| Characteristic | Symbol | Value | Units |
|---|-----------------|-------------|--------------------|
| Total Power Dissipation (Note 1) | P_D | 150 | mW |
| Thermal Resistance, Junction to Ambient | $R_{\theta JA}$ | 833 | $^\circ\text{C/W}$ |
| Operating and Storage Temperature Range | T_J, T_{STG} | -55 to +150 | $^\circ\text{C}$ |

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

| Characteristic | Symbol | Min | Typ | Max | Unit | Test Condition |
|-------------------------------------|--------------|------|-----|-----------|---------------|---|
| OFF CHARACTERISTICS (Note 5) | | | | | | |
| Drain-Source Breakdown Voltage | BV_{DSS} | -20 | — | — | V | $V_{GS} = 0\text{V}, I_D = -250\text{mA}$ |
| Zero Gate Voltage Drain Current | I_{DSS} | — | — | -1.0 | μA | $V_{DS} = -20\text{V}, V_{GS} = 0\text{V}$ |
| Gate-Source Leakage | I_{GSS} | — | — | ± 1.0 | μA | $V_{GS} = \pm 4.5\text{V}, V_{DS} = 0\text{V}$ |
| ON CHARACTERISTICS (Note 5) | | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | -0.5 | — | -1.0 | V | $V_{DS} = V_{GS}, I_D = -250\mu\text{A}$ |
| Static Drain-Source On-Resistance | $R_{DS(on)}$ | — | 0.7 | 1.1 | Ω | $V_{GS} = -4.5\text{V}, I_D = -430\text{mA}$ |
| | | — | 1.1 | 1.6 | | $V_{GS} = -2.5\text{V}, I_D = -300\text{mA}$ |
| | | — | 1.7 | 2.6 | | $V_{GS} = -1.8\text{V}, I_D = -150\text{mA}$ |
| Forward Transfer Admittance | $ Y_{fs} $ | 200 | — | — | ms | $V_{DS} = 10\text{V}, I_D = 0.2\text{A}$ |
| Diode Forward Voltage (Note 5) | V_{SD} | — | — | -1.4 | V | $V_{GS} = 0\text{V}, I_S = -115\text{mA}$ |
| DYNAMIC CHARACTERISTICS | | | | | | |
| Input Capacitance | C_{iss} | — | — | 175 | pF | $V_{DS} = -16\text{V}, V_{GS} = 0\text{V}$ $f = 1.0\text{MHz}$ |
| Output Capacitance | C_{oss} | — | — | 30 | pF | |
| Reverse Transfer Capacitance | C_{rss} | — | — | 20 | pF | |

- Notes:
1. Device mounted on FR-4 PCB.
 2. No purposefully added lead.
 3. Pulse width $\leq 10\mu\text{s}$, Duty Cycle $\leq 1\%$
 4. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
 5. Short duration pulse test used to minimize self-heating effect.

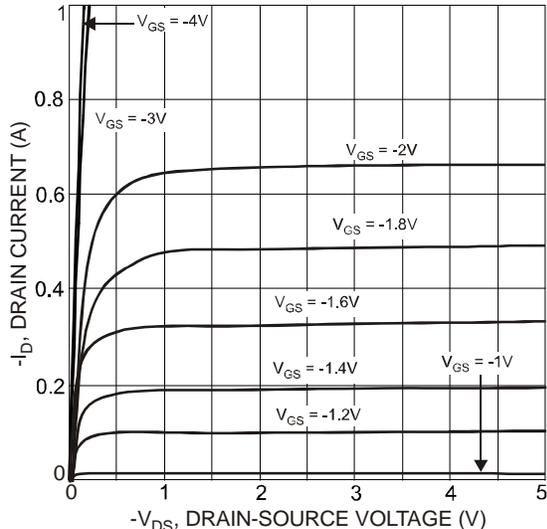


Fig. 1 Typical Output Characteristics

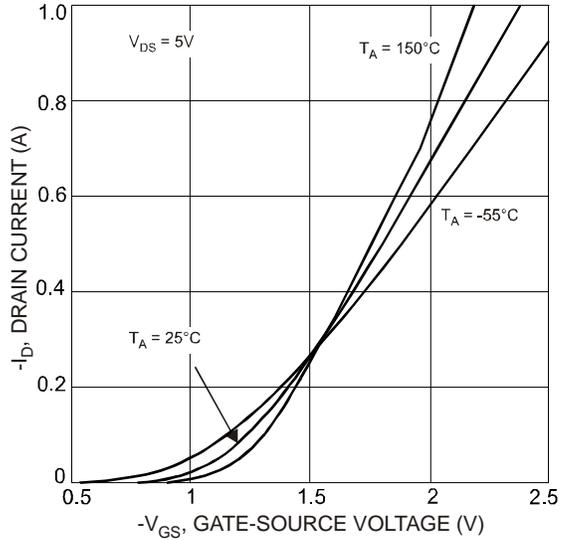


Fig. 2 Typical Transfer Characteristics

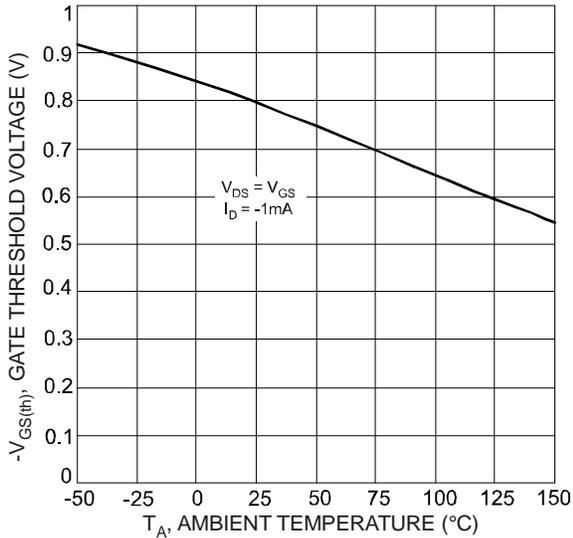


Fig. 3 Gate Threshold Voltage vs. Ambient Temperature

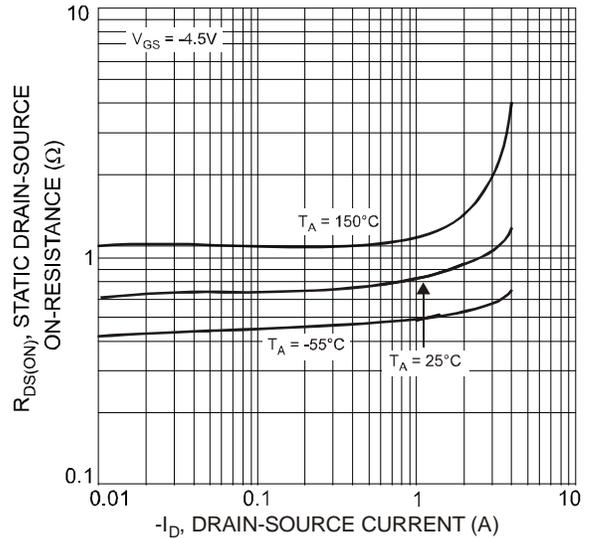


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

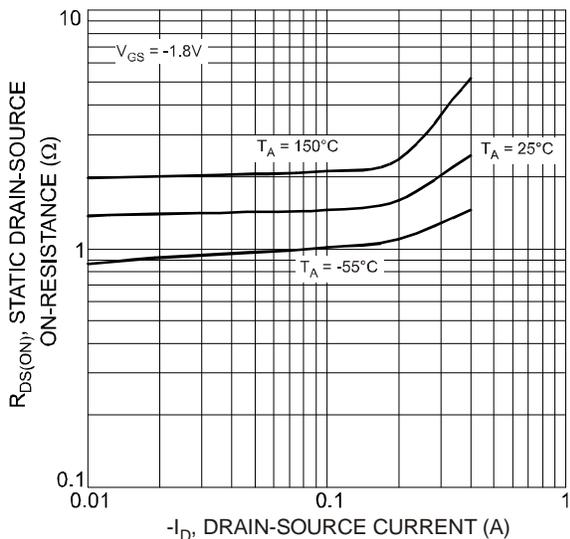


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current

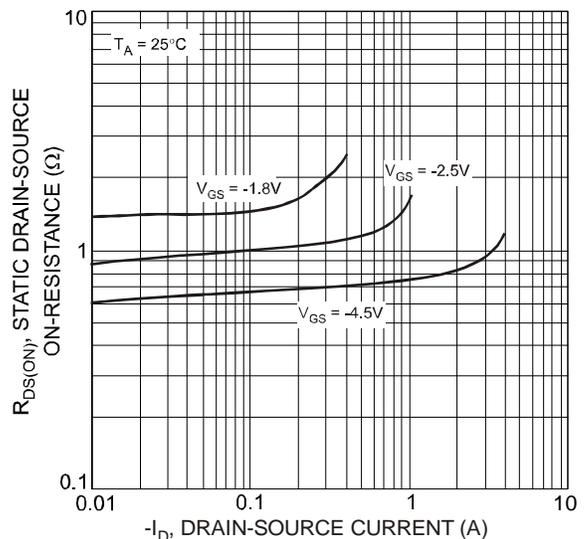


Fig. 6 Static Drain-Source On-Resistance vs. Drain-Source Current

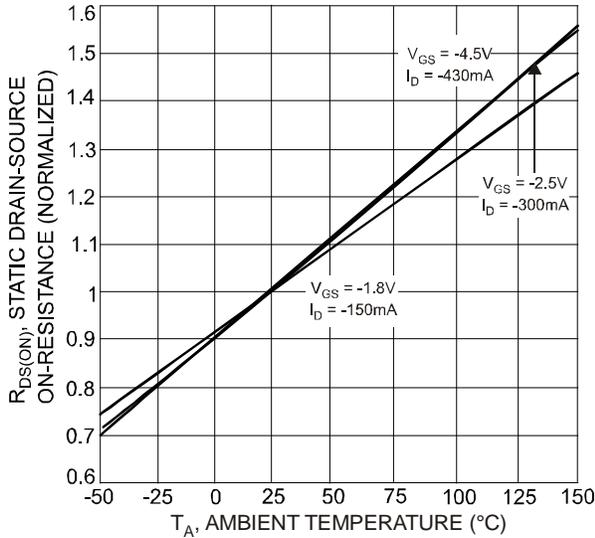


Fig. 7 Static Drain-Source On-State Resistance vs. Ambient Temperature

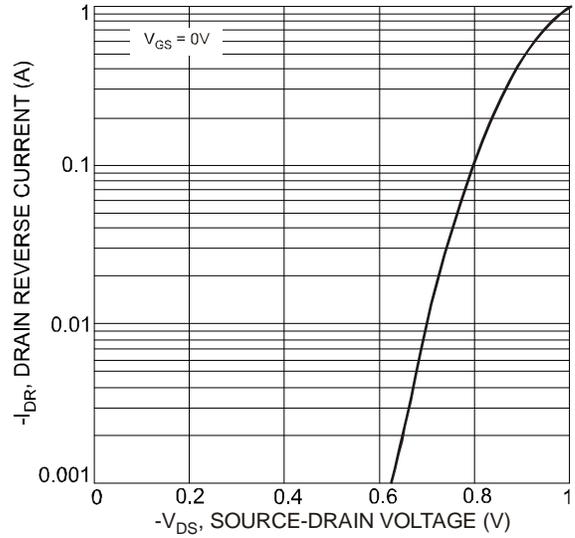


Fig. 8 Reverse Drain Current vs. Source-Drain Voltage

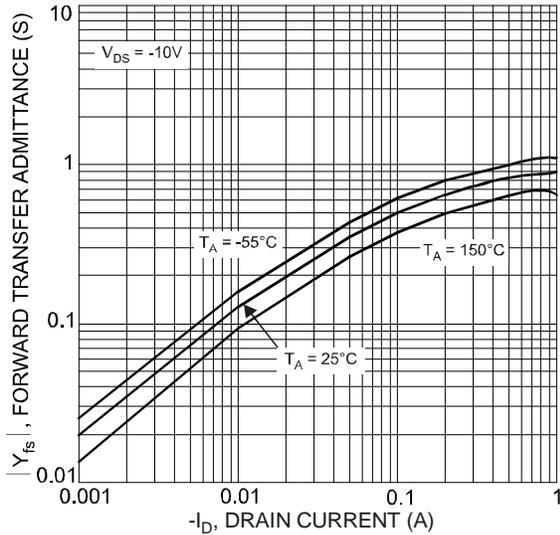


Fig. 9 Forward Transfer Admittance vs. Drain Current

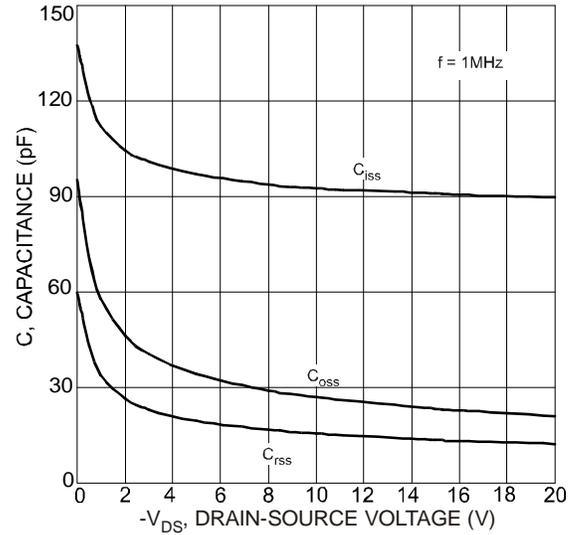


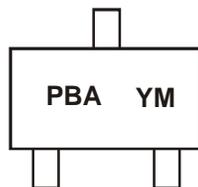
Fig. 10 Typical Capacitance

Ordering Information (Note 6)

| Part Number | Case | Packaging |
|-------------|---------|------------------|
| DMP22D6UT-7 | SOT-523 | 3000/Tape & Reel |

Notes: 6. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

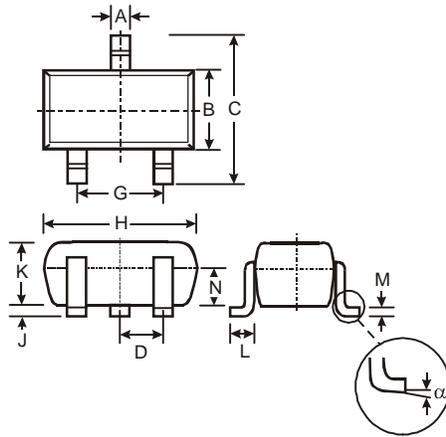
Marking Information



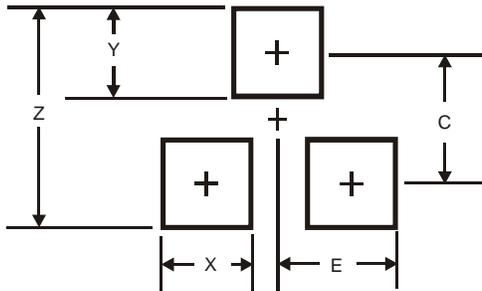
PBA = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: V = 2008)
 M = Month (ex: 9 = September)

Date Code Key

| Year | 2008 | 2009 | 2010 | 2011 | 2012 | 2013 | 2014 | 2015 | | | | |
|-------|------|------|------|------|------|------|------|------|-----|-----|-----|-----|
| Code | V | W | X | Y | Z | A | B | C | | | | |
| Month | Jan | Feb | Mar | Apr | May | Jun | Jul | Aug | Sep | Oct | Nov | Dec |
| Code | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | O | N | D |

Package Outline Dimensions


| SOT-523 | | | |
|----------------------|------|------|------|
| Dim | Min | Max | Typ |
| A | 0.15 | 0.30 | 0.22 |
| B | 0.75 | 0.85 | 0.80 |
| C | 1.45 | 1.75 | 1.60 |
| D | — | — | 0.50 |
| G | 0.90 | 1.10 | 1.00 |
| H | 1.50 | 1.70 | 1.60 |
| J | 0.00 | 0.10 | 0.05 |
| K | 0.60 | 0.80 | 0.75 |
| L | 0.10 | 0.30 | 0.22 |
| M | 0.10 | 0.20 | 0.12 |
| N | 0.45 | 0.65 | 0.50 |
| α | 0° | 8° | — |
| All Dimensions in mm | | | |

Suggested Pad Layout


| Dimensions | Value (in mm) |
|------------|---------------|
| Z | 1.8 |
| X | 0.4 |
| Y | 0.51 |
| C | 1.3 |
| E | 0.7 |

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Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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